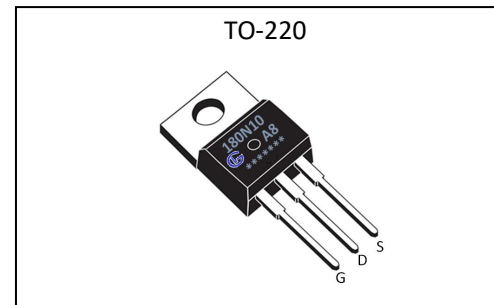


General Description

The GL180N10A8 uses Super Trench technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification. The package form is TO-220, which accords with the RoHS standard.

V_{DSS}	100	V
I_D	180	A
P_D	300	W
$R_{DS(ON)MAX}$	4.5	m Ω

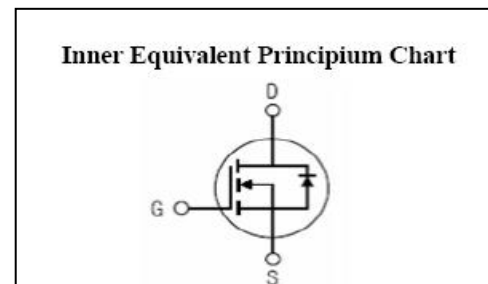


Features

- $R_{DS(ON)} < 4.5m\Omega$ @ $V_{GS}=10V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Applications

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Absolute (Tc= 25°C unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	100	V
I_D	Continuous Drain Current	180	A
I_{DM}	Pulsed Drain Current	720	A
V_{GS}	Gate-to-Source Voltage	± 20	V
P_D	Power Dissipation	300	W
E_{AS}	Single pulse avalanche energy ^{a5}	1000	mJ
T_J, T_{stg}	Operating Junction and Storage Temperature Range	175, -55 to 175	°C



GL180N10A8

GL Silicon N-Channel Super Trench Power MOSFET

Electrical Characteristics (Tc= 25°C unless otherwise specified)

OFF Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V _{DSS}	Drain to Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	--	--	V
I _{DSS}	Drain to Source Leakage Current	V _{DS} =100V, V _{GS} = 0V, T _a =25°C	--	--	1.0	μA
I _{GSS(F)}	Gate to Source Forward Leakage	V _{GS} = +20V	--	--	0.1	μA
I _{GSS(R)}	Gate to Source Reverse Leakage	V _{GS} = -20V	--	--	-0.1	μA

ON Characteristics^{a3}

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
R _{DS(ON)}	Drain-to-Source On-Resistance	V _{GS} =10V, I _D =100A	--	--	4.5	mΩ
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	--	4.5	V

Pulse width tp≤380μs, δ≤2%

Dynamic Characteristics^{a4}

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =50A	40	--	--	S
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =50V f=1.0MHz	--	7200	--	pF
C _{oss}	Output Capacitance		--	1500	--	
C _{rss}	Reverse Transfer Capacitance		--	60	--	

Resistive Switching Characteristics^{a4}

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =50V, I _D =100A V _{GS} =10V, R _G =1.6Ω	--	32	--	ns
t _r	Rise Time		--	30	--	
t _{d(OFF)}	Turn-Off Delay Time		--	95	--	
t _f	Fall Time		--	36	--	
Q _g	Total Gate Charge	V _{DD} =50V, I _D =100A V _{GS} =10V	--	130	--	nC
Q _{gs}	Gate to Source Charge		--	33	--	
Q _{gd}	Gate to Drain ("Miller") Charge		--	29	--	



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Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current ^{a2} (Body Diode)		--	--	180	A
V_{SD}	Diode Forward Voltage ^{a3}	$I_S=180A, V_{GS}=0V$	--	--	1.2	V

Symbol	Parameter	Typ.	Units
$R_{\theta JC}$	Junction-to-Case ^{a2}	0.5	°C/W

^{a1}: Repetitive Rating: Pulse width limited by maximum junction temperature.

^{a2}: Surface Mounted on FR4 Board, $t \leq 10\text{sec}$.

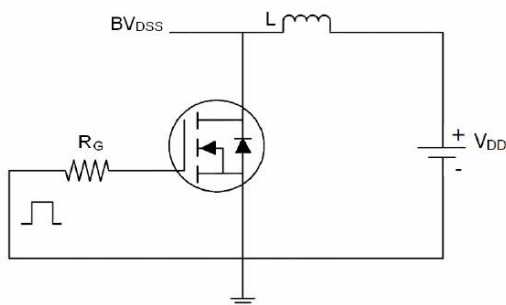
^{a3}: Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.

^{a4}: Guaranteed by design, not subject to production

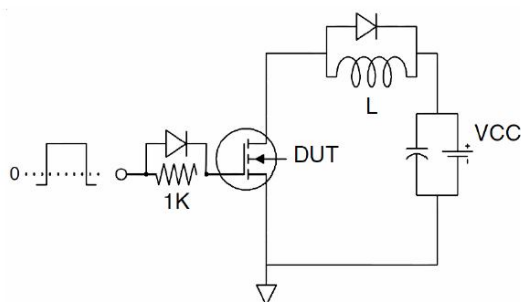
^{a5}: EAS condition: $T_j=25^\circ\text{C}, V_{DD}=50V, V_G=10V, L=0.5\text{mH}, R_g=25\Omega$

Test circuit

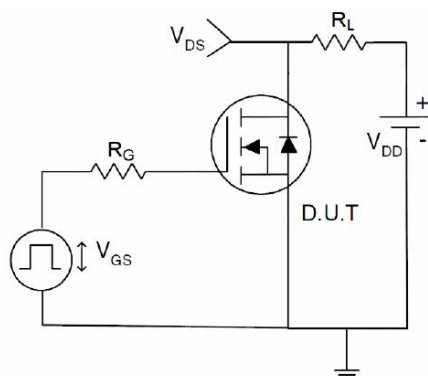
1) EAS test Circuit



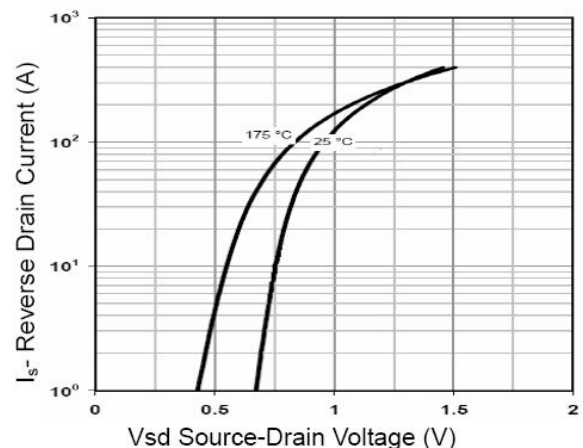
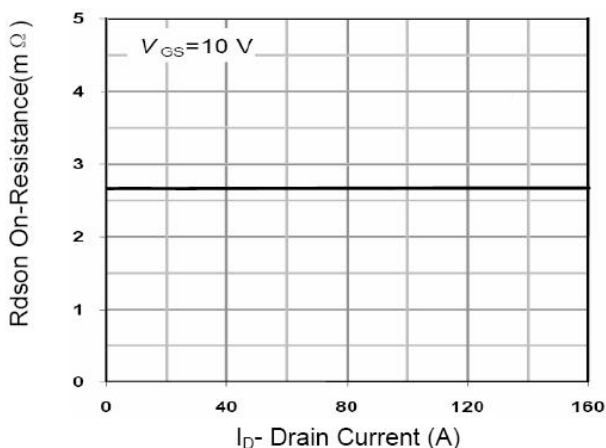
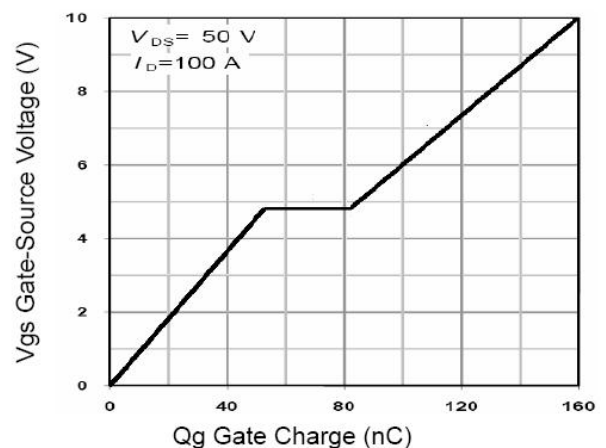
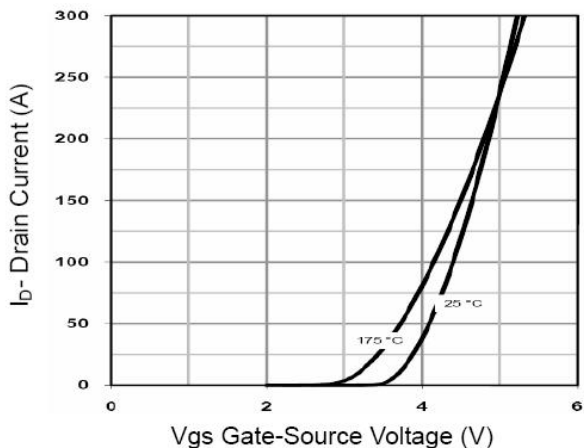
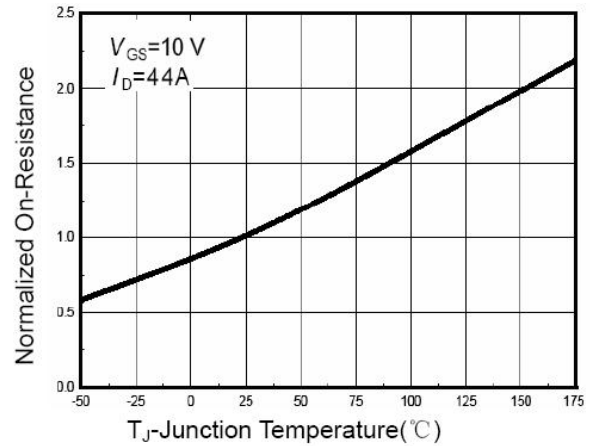
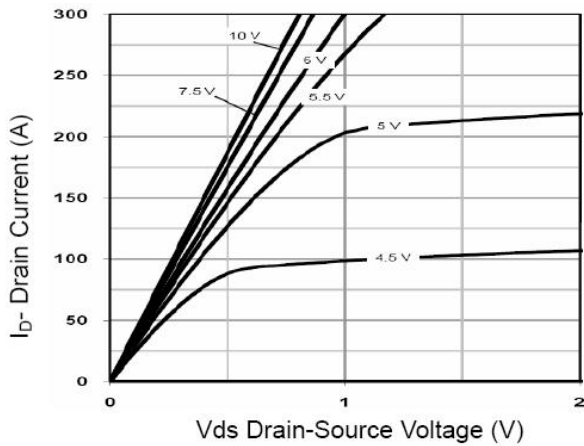
2) Gate charge test Circuit



3) Switch Time Test Circuit



Characteristics Curve



GL Silicon N-Channel Super Trench Power MOSFET

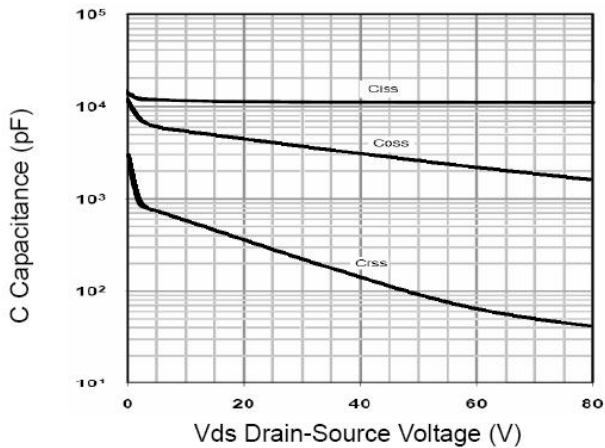


Figure 7 Capacitance vs Vds

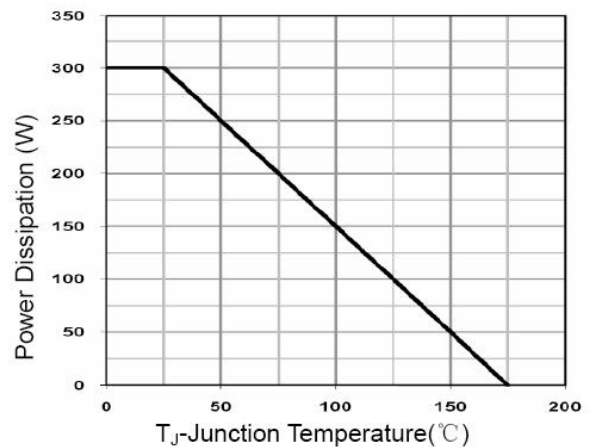


Figure 9 Power De-rating

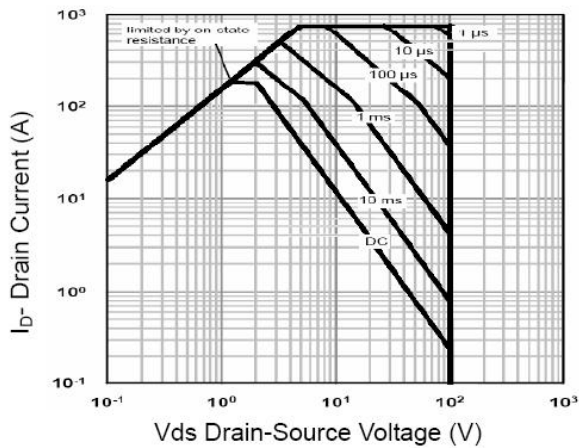


Figure 8 Safe Operation Area

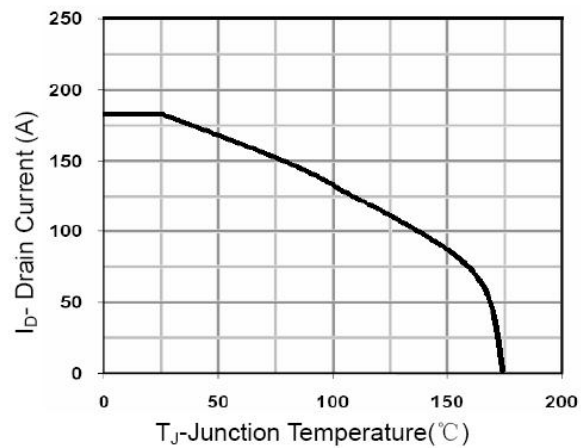


Figure 10 Current De-rating

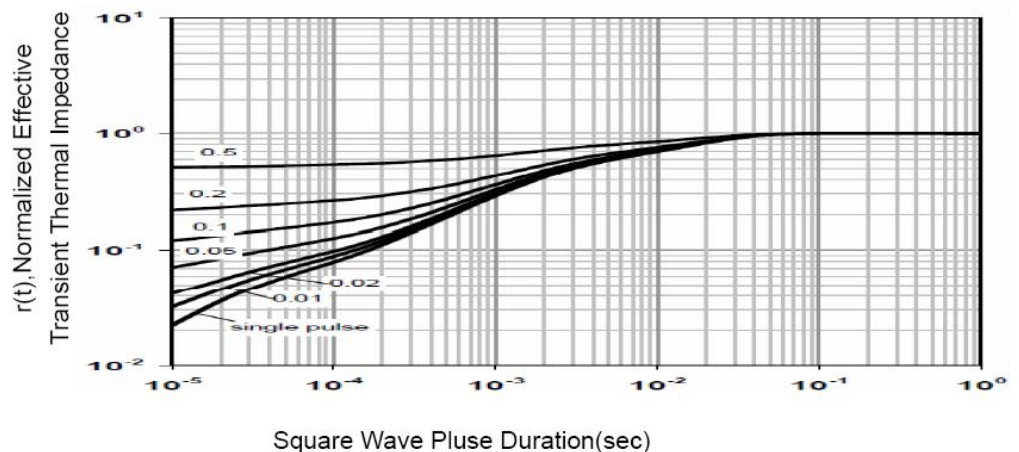


Figure 11 Normalized Maximum Transient Thermal Impedance